

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IRF3707Z, IIRF3707Z

• FEATURES

- Low drain-source on-resistance: R⊳s(on) ≤9.5mΩ
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

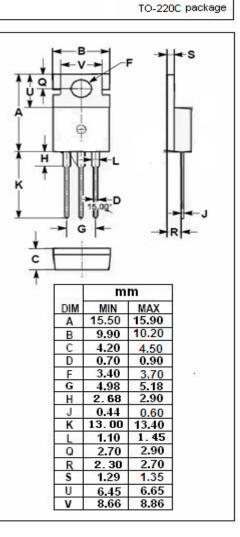
• reliable device for use in a wide variety of applications

ABSOLUTE MAXIMUM RATINGS(Ta=23 C)							
SYMBOL	MBOL PARAMETER		UNIT				
VDSS	Drain-Source Voltage	30	V				
V _{GS}	Gate-Source Voltage	±20	V				
ID	Drain Current-Continuous	59	А				
I _{DM}	Drain Current-Single Pulsed	230	А				
PD	Total Dissipation @T _c =25°C	57					
Tj	Max. Operating Junction Temperature		°C				
T _{stg}	Storage Temperature	-55~175	°C				

• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

pin 1, Gate 1 2 3 2, Drain

3, Source



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	2.653	°C /W
Rth(ch-a) Channel-to-ambient thermal resistance		62	°C /W

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ELECTRICAL CHARACTERISTICS

 $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID = 250μA	30			v
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =25 μ A	1.35		2.25	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =21A			9.5	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V; V _{GS} = 0V			1.0	μA
Vsd	Diode forward voltage	Is =17A, V _{GS} = 0 V			1.0	V

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